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RFM15N12, RFM15N15, RFP15N12, RFP15N15

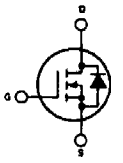
N-Channel Enhancement-Mode Power Field-Effect Transistors

15 A, 120 V — 150 V

$r_{DS}(on)$: 0.15 Ω

Features:

- *SOA is power-dissipation limited*
- *Nanosecond switching speeds*
- *Linear transfer characteristics*
- *High input impedance*
- *Majority carrier device*



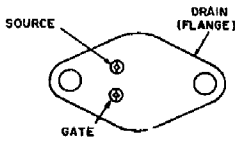
N-Channel Enhancement Mode

The RFM15N12 and RFM15N15 and the RFP15N12 and RFP15N15* are n-channel enhancement-mode silicon-gate power field-effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

The RFM-types are supplied in the JEDEC TO-204AA steel package and the RFP-types in the JEDEC TO-220AB plastic package.

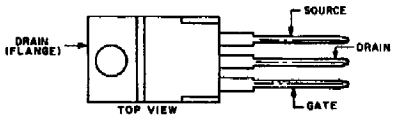
TERMINAL DESIGNATIONS

RFM15N12
RFM15N15



JEDEC TO-204AA

RFP15N12
RFP15N15



JEDEC TO-220AB

MAXIMUM RATINGS, *Absolute-Maximum Values (T_c=25°C):*

		RFM15N12	RFM15N15	RFP15N12	RFP15N15	
DRAIN-SOURCE VOLTAGE	V_{DSS}	120	150	120	150	V
DRAIN-GATE VOLTAGE (R_{GS}=1 MΩ)	V_{DGR}	120	150	120	150	V
GATE-SOURCE VOLTAGE	V_{GS}	±20				V
DRAIN CURRENT RMS Continuous	I_D	15				A
Pulsed	I_{DM}	40				A
POWER DISSIPATION						
@ T_C=25°C	P_T	100	100	75	75	W
Derate above T_C=25°C		0.80	0.80	0.6	0.6	W/°C
OPERATING AND STORAGE TEMPERATURE	T_J, T_{stg}	−55 to +150				°C

ELECTRICAL CHARACTERISTICS *At Case Temperature (T_c) = 25° C unless otherwise specified*

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	LIMITS RFM15N12 RFP15N12 MIN.	MAX.	LIMITS RFM15N15 RFP15N15 MIN.	MAX.	UNITS
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 1 mA, V_{GS} = 0	120	—	150	—	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, I_D = 1 mA	2	4	2	4	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V	—	1	—	—	μA
		V_{DS} = 120 V	—	—	—	1	
		T_C = 125° C					
		V_{DS} = 100 V	—	50	—	—	
		V_{DS} = 120 V	—	—	—	50	
Gate-Source Leakage Current	I_{GSS}	V_{GS} = ± 20 V, V_{DS} = 0	—	100	—	100	nA
Drain-Source On Voltage	$V_{DS(on)}$*	I_D = 7.5 A, V_{GS} = 10 V	—	1.125	—	1.125	V
		I_D = 15 A, V_{GS} = 10 V	—	3	—	3	
Static Drain-Source On Resistance	$r_{DS(on)}$*	I_D = 7.5 A, V_{GS} = 10 V	—	0.15	—	0.15	Ω
Forward Transconductance	g_{fs}*	V_{DS} = 10 V, I_D = 7.5 A	5	—	5	—	mho
Input Capacitance	C_{iss}	V_{DS} = 25 V	—	1700	—	1700	pF
Output Capacitance	C_{oss}	V_{GS} = 0 V	—	750	—	750	
Reverse Transfer Capacitance	C_{rss}	f = 1MHz	—	350	—	350	
Turn-On Delay Time	t_d(on)	V_{DD}=75 V	50(typ.)	75	50(typ.)	75	ns
Rise Time	t_r	I_D = 7.5 A	150(typ.)	225	150(typ.)	225	
Turn-Off Delay Time	t_d(off)	$R_{gen} = R_{gs}$ = 50 Ω	185(typ.)	280	185(typ.)	280	
Fall Time	t_f	V_{GS} = 10 V	125(typ.)	190	125(typ.)	190	
Thermal Resistance Junction-to-Case	RθJC	RFM15N12, RFM15N15	—	1.25	—	1.25	°C/W
		RFP15N12, RFP15N15	—	1.67	—	1.67	

*Pulsed: Pulse duration = 300 μs max., duty cycle = 2%.

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS RFM15N12 RFP15N12 MIN.	MAX.	LIMITS RFM15N15 RFP15N15 MIN.	MAX.	UNITS
Diode Forward Voltage	V_{SD}	I_{SD}=7.5 A	—	1.4	—	1.4	V
Reverse Recovery Time	t_{rr}	I_F=4 A, d_{IF}/d_t=100 A/μs	200(typ)		200(typ)		ns

*Pulse Test: Width ≤ 300 μs, duty cycle ≤ 2%.